Amendments to the Claims:

1.   (Currently Amended) A method for verifying ~~reticle enhancement technique latent~~ post-optical proximity corrected mask wafer image sensitivity to ~~mask~~ reticle manufacturing errors, said method comprising: ~~revising a polygon based on mask CD distributions to provide~~ statistically modifying layout polygons based on reticle critical dimension specifications to construct a ~~virtual~~ statistical virtual mask; obtaining ~~response function statistical parameters based on the~~ virtual mask image response function statistical parameters; and comparing the statistical parameters to ~~design rule~~ process tolerance requirements.

2.   (Currently Amended) A method as recited in claim 1, further comprising forming ~~an~~ a simulated image of the statistical virtual mask.

3.   (Currently Amended) A method as recited in claim 2, further comprising calculating response functions based on the ~~aerial and/or latent image simulation~~ simulated image.

4.   (Currently Amended) A method as recited in claim 3, further comprising collecting ~~measurements~~ simulated image critical dimensions and calculating statistical parameters based on the response functions.

5.   (Currently Amended) A method as recited in claim 4, further comprising comparing ~~the statistical parameters with design rule~~ simulated wafer critical dimension distributions with process tolerance requirements.

Serial No. 10/800,219
Art Unit: 2825
Page 9

6.   (Currently Amended) A method as recited in claim 1, further comprising obtaining the statistical virtual mask by using ~~mask~~ reticle critical dimension ~~CD distribution~~ specifications to induce reticle manufacturing statistical variations to layouts which have passed through an ~~OPC~~ optical proximity correction procedure.

7.   (Currently Amended) A method as recited in claim 6, further comprising at least one of moving fragments of a polygon and re-sizing primitives of a post-optical proximity correction polygon.

8.   (Currently Amended) A method as recited in claim 6, further comprising moving fragments of a post-optical proximity correction polygon based on a randomly generated number from ~~mask CD distribution~~ a reticle critical dimension specification.

9.   (Currently Amended) A method as recited in claim 6, further comprising re-sizing primitives depending on ~~mask CD distribution~~ a reticle critical dimension specification.

10.   (Currently Amended) A yield prediction tool for mask quality specifications, said tool comprising means for ~~revising a polygon based on mask CD distributions to provide~~ statistically modifying layout polygons based on reticle critical dimension specifcations to construct a statistical virtual mask, means for obtaining ~~statistical parameters based on the~~ virtual mask imaging response function statistical parameters; and means for comparing the statistical response parameters to ~~design rule~~ process tolerance requirements.

Serial No. 10/800,219
Art Unit: 2825
Page 10

11.   (Currently Amended) A tool as recited in claim 10, further comprising means for simulating an aerial and/or latent image of the <u>statistical formed</u> virtual mask.

12.   (Original) A tool as recited in claim 11, further comprising means for calculating response functions based on the simulated image.

13.   (Currently Amended) A tool as recited in claim 12, further comprising means for collecting ~~measurements~~ <u>simulated image critical dimensions</u> and calculating statistical parameters based on the response functions.

14.   (Currently Amended) A tool as recited in claim 13, further comprising means for comparing ~~the statistical parameters with design rule~~ <u>simulated wafer critical dimension distributions with process tolerance</u> requirements.

15.   (Currently Amended) A tool as recited in claim 10, further comprising means for obtaining the <u>statistical</u> virtual mask by using ~~mask~~ <u>riticle critical dimension</u> ~~CD distribution~~ <u>specifications</u> to statistically vary layouts which have passed through an ~~OPC~~ <u>optical proximity correction</u> procedure.

16.   (Currently Amended) A tool as recited in claim 15, further comprising means for at least one of moving fragments of a polygon and re-sizing primitives <u>of a post-optical proximity correction polygon.</u>

Serial No. 10/800,219
Art Unit: 2825
Page 11

17.   (Currently Amended) A tool as recited in claim 15, further comprising means for moving fragments of a <u>post-optical proximity correction</u> polygon based on a randomly generated number from ~~mask CD distribution~~ <u>a reticle critical dimension specification</u>.

18.   (Currently Amended) A tool as recited in claim 15, further comprising means for re-sizing primitives depending on ~~mask CD distribution~~ <u>a reticle critical dimension specification</u>.

Serial No. 10/800,219
Art Unit: 2825
Page 12